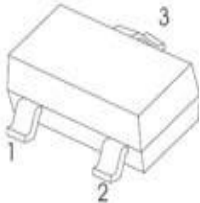
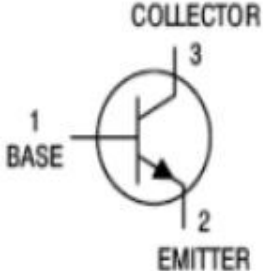


TRANSISTOR (PNP)	SOT-23 Plastic-Encapsulate Transistors																																				
<p style="text-align: center;"><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p style="text-align: center;">Marking :2T</p>	<p style="text-align: center;">Features</p> <ul style="list-style-type: none"> <li>※ Complimentary to MMBT4401</li> <li>※ Collector Current: Ic=0.6A</li> <li>※ Switching Transistor</li> </ul>																																				
<p><b>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</b></p> <table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th style="text-align: center;">Parameter</th> <th style="text-align: center;">Symbol</th> <th style="text-align: center;">Value</th> <th style="text-align: center;">Unit</th> </tr> </thead> <tbody> <tr> <td>Collector-Base Voltage</td> <td style="text-align: center;">VCBO</td> <td style="text-align: center;">-60</td> <td style="text-align: center;">V</td> </tr> <tr> <td>Collector-Emitter Voltage</td> <td style="text-align: center;">VCEO</td> <td style="text-align: center;">-60</td> <td style="text-align: center;">V</td> </tr> <tr> <td>Emitter-Base Voltage</td> <td style="text-align: center;">VEBO</td> <td style="text-align: center;">-6</td> <td style="text-align: center;">V</td> </tr> <tr> <td>Collector Current</td> <td style="text-align: center;">IC</td> <td style="text-align: center;">-600</td> <td style="text-align: center;">mA</td> </tr> <tr> <td>Collector Power Dissipation</td> <td style="text-align: center;">PC</td> <td style="text-align: center;">300</td> <td style="text-align: center;">mW</td> </tr> <tr> <td>Thermal Resistance From Junction To Ambient</td> <td style="text-align: center;">RθJA</td> <td style="text-align: center;">417</td> <td style="text-align: center;">°C/W</td> </tr> <tr> <td>Junction Temperature</td> <td style="text-align: center;">Tj</td> <td style="text-align: center;">150</td> <td style="text-align: center;">°C</td> </tr> <tr> <td>Storage Temperature</td> <td style="text-align: center;">Tstg</td> <td style="text-align: center;">-55~+150</td> <td style="text-align: center;">°C</td> </tr> </tbody> </table>		Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	-60	V	Collector-Emitter Voltage	VCEO	-60	V	Emitter-Base Voltage	VEBO	-6	V	Collector Current	IC	-600	mA	Collector Power Dissipation	PC	300	mW	Thermal Resistance From Junction To Ambient	RθJA	417	°C/W	Junction Temperature	Tj	150	°C	Storage Temperature	Tstg	-55~+150	°C
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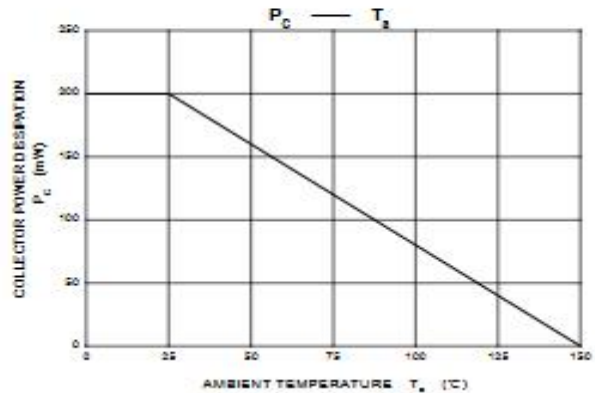
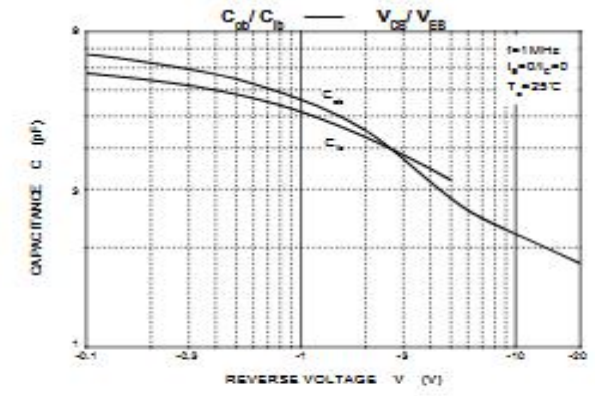
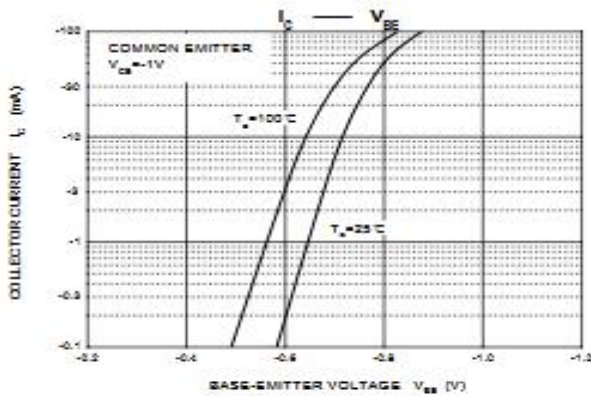
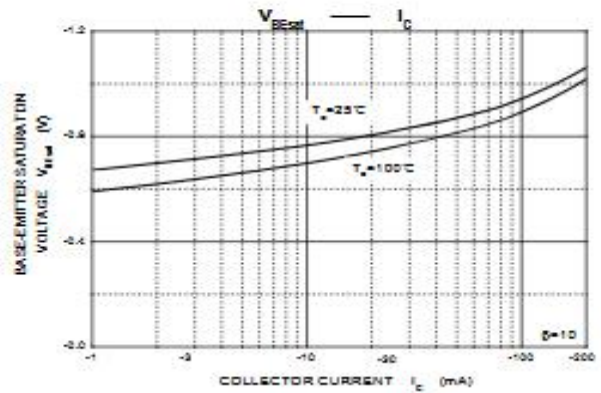
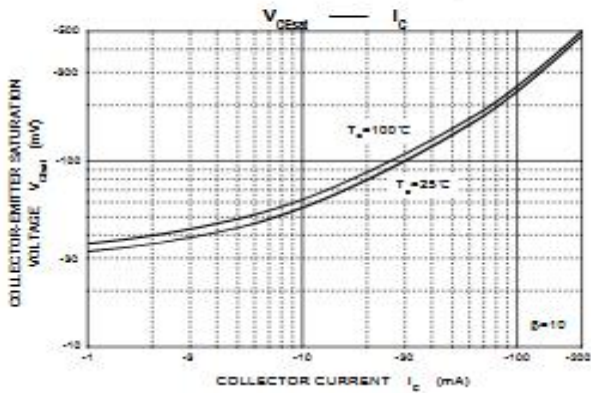
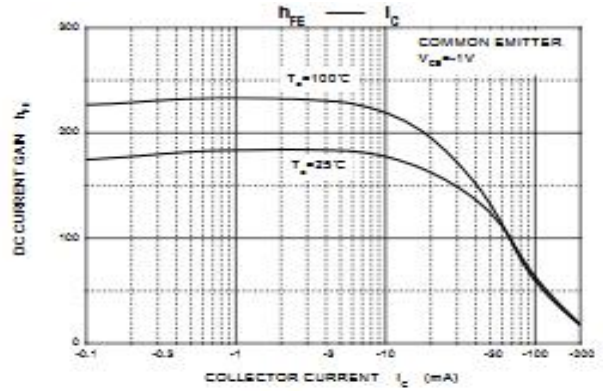
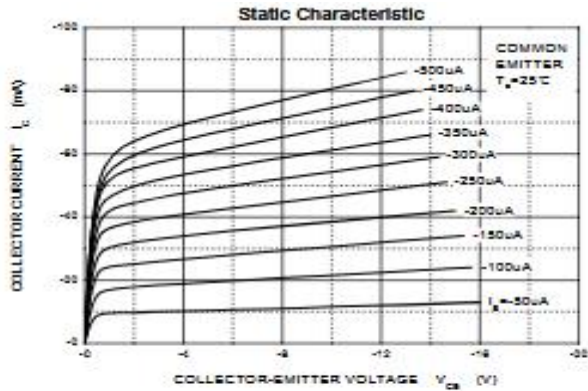
**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100µA, IE=0	-60	-102	-200	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-60	-82	-100	V
Emitter-base breakdown voltage	V(BR)EBO	IE= -100µA, IC=0	-6	-8.5	-30	V
Collector cut-off current	ICBO	VCB= -50 V , IE=0			-0.1	µA
Collector cut-off current	ICEO	VCB= -35V , IE=0			-0.1	µA
Emitter cut-off current	IEBO	VEB= -6V , IC=0			-0.1	µA
DC current gain	hFE	VCE= -10V, IC= -150mA	100		300	
	hFE	VCE= -1V, IC= -1mA	60			
Collector-emitter saturation voltage	VCE(sat)	IC= -500 mA, IB= -50mA			-1.6	V
Base-emitter saturation voltage	VBE(sat)	IC= -500 mA, IB= -50mA			-2.6	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	200			MHz
Delay time	td	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			15	ns
Rise time	tr	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			25	ns
Storage time	ts	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			225	ns
Fall time	tf	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			60	ns

**CLASSIFICATION OF hFE**

<b>HFE</b>	<b>100-300</b>	
<b>Rank</b>	<b>L</b>	<b>H</b>
<b>Range</b>	<b>100-200</b>	<b>200-300</b>

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)